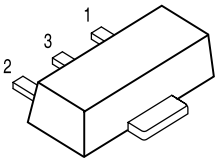
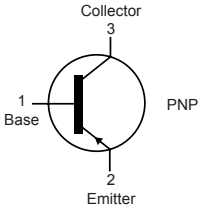
PNP Medium Power Transistor





Features:

- Low Voltage
- High Current

Pin Configuration:
1. Base
2. Emitter
3. Collector

Applications:

- Low voltage,high current LF applications
- Complement to BC868

Maximum Ratings

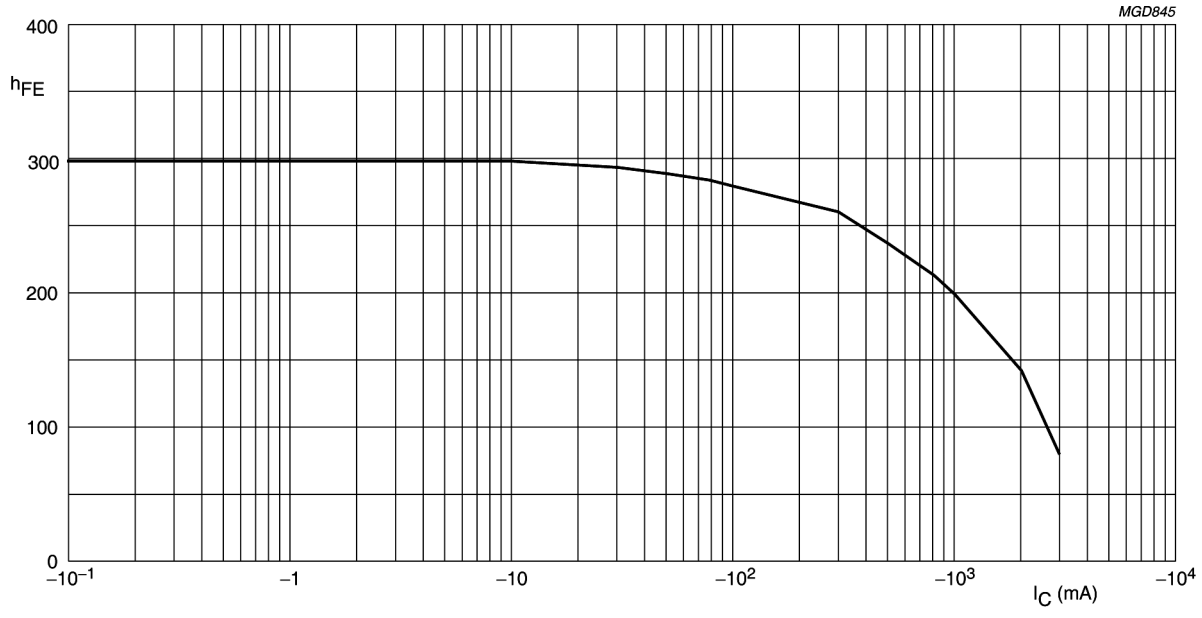
Parameter	Symbol	Value	Unit
Collector - Base Voltage	V_{CBO}	-32	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{ebo}	-5	
DC Collector Current	I_C	-1	A
Collector Current - Peak	I_{CM}	-2	
Peak Base Current	I_{BM}	-200	mA
Total Power Dissipation (T_{AMB}<25°C)	P_{TOT}	1.35	W
Junction and Storage Temperature	T_j, T_{stg}	-65 to +150	°C

Electrical Characteristics (T_a = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-25V, I_E=0 V_{CB}=-25V, I_E=0, T_j=150°C			-100 -10	nA µA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-10	nA
DC Current Gain	h_{FE}	V_{CE}=-10V, I_C=-5mA V_{CE}=-1V, I_C=-500mA V_{CE}=-1V, I_C=-1A	50 100 60		375	
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1A, I_B=-100mA			-0.5	V
Base Emitter Voltage	V_{BE}	I_C=-1A, V_{CE}=-1V			-1	
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=100MHz	40			MHz

Typical Characteristics: T_a=25°C unless otherwise specified

Ratings & Characteristic Curves



V_{CE} = −1 V.

DC current gain; typical values

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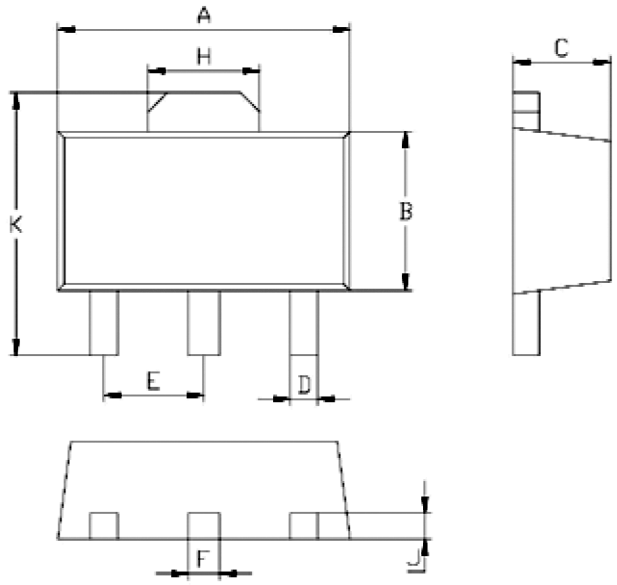
Package Outline

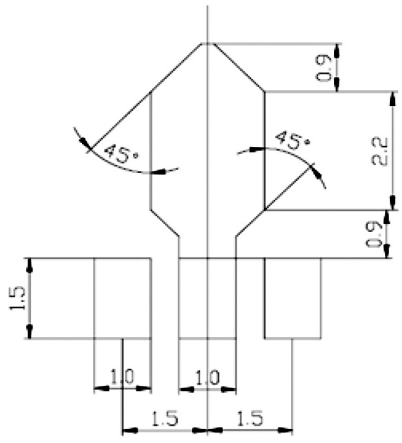
Plastic surface mounted package



Dimensions	Min.	Max.
A	4.5	4.7
B	2.3	2.7
C	1.5 Typical	
D	0.35	0.55
E	1.4	1.6
F	0.4	0.6
H	1.55	1.75
J	0.4 Typical	
K	4.15	4.25

Dimensions : Millimetres

Soldering Footprint



Dimensions : Millimetres

Part Number Table

Description	Part Number
Transistor, PNP, 1A, 20V, SOT-89	BC869